

The S-8239B Series is an overcurrent monitoring IC for multi-serial-cell pack including high-accuracy voltage detection circuits and delay circuits.

The S-8239B Series is suitable for protection of lithium-ion / lithium polymer rechargeable battery packs from overcurrent.

## ■ Features

- Built-in high-accuracy voltage detection circuit

Overcurrent 1 detection voltage*1	0.04 V to 0.30 V (10 mV step)	Accuracy $\pm 15$ mV
Overcurrent 2 detection voltage	0.1 V to 0.7 V (100 mV step)	Accuracy $\pm 100$ mV
Overcurrent 3 detection voltage	1.2 V (Fixed)	Accuracy $\pm 300$ mV
- Built-in three-step overcurrent detection circuit: Overcurrent 1, overcurrent 2, overcurrent 3
- Overcurrent 3 detection function: Available, unavailable
- UVLO (under voltage lock out) function

UVLO detection voltage	2.0 V (Fixed)	Accuracy $\pm 100$ mV
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- High-withstand voltage: VM pin, DO pin: Absolute maximum rating 28 V
- Delay times are generated only by an internal circuit (External capacitors are unnecessary).
- Low current consumption

During normal operation:	7.0 $\mu$ A max.
During power-down:	0.1 $\mu$ A max.
- Output logic: Active "L"
- Wide operation temperature range: Ta =  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$
- Lead-free (Sn 100%), halogen-free

\*1. Overcurrent 1 detection voltage  $\leq 0.06$  V should be satisfied in the case of overcurrent 2 detection voltage = 0.1 V.  
Overcurrent 1 detection voltage  $\leq 0.85 \times$  overcurrent 2 detection voltage  $- 0.05$  V should be satisfied in the case of overcurrent 2 detection voltage  $\geq 0.2$  V.

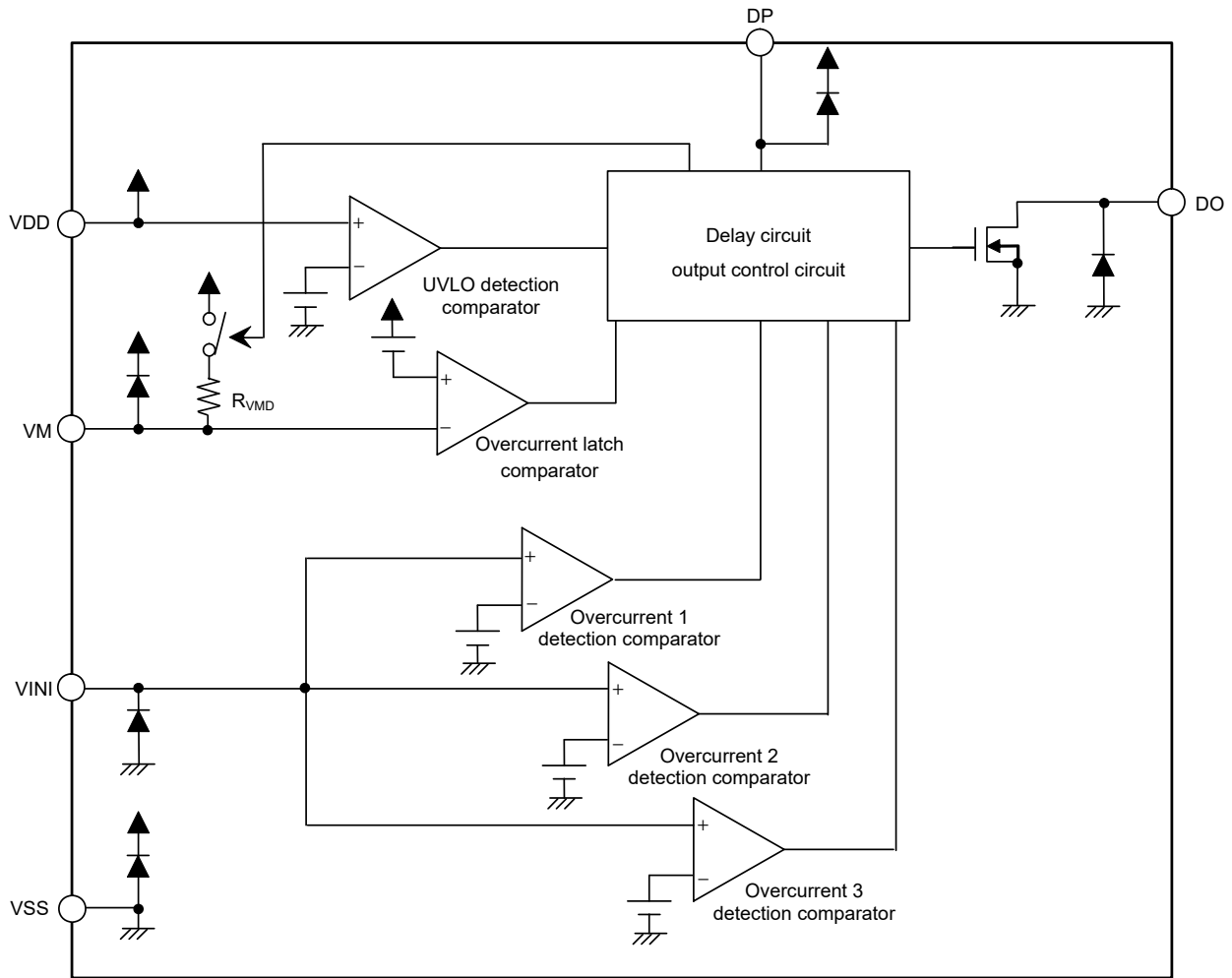
## ■ Applications

- Lithium-ion rechargeable battery pack
- Lithium polymer rechargeable battery pack

## ■ Package

- SOT-23-6

■ Block Diagram

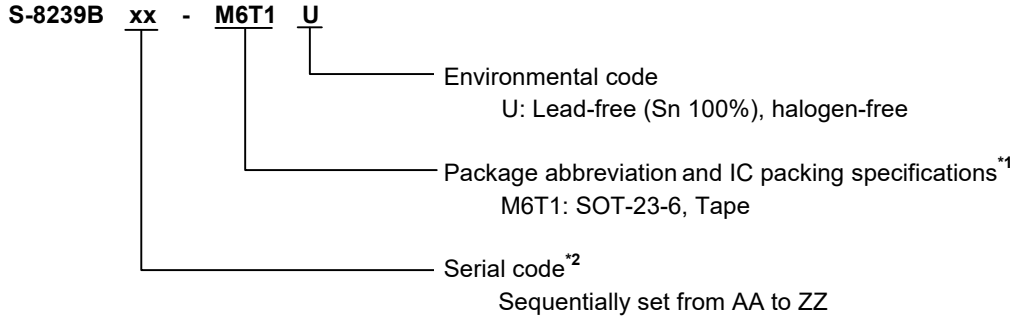


**Remark** All the diodes shown in the figure are parasitic diodes.

Figure 1

**■ Product Name Structure**

**1. Product name**



\*1. Refer to the tape drawing.  
 \*2. Refer to "3. Product name list".

**2. Package**

**Table 1 Package Drawing Codes**

Package Name	Dimension	Tape	Reel
SOT-23-6	MP006-A-P-SD	MP006-A-C-SD	MP006-A-R-SD

**3. Product name list**

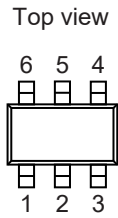
**Table 2**

Product Name	Overcurrent 1 Detection Voltage [V <sub>DIOV1</sub> ]	Overcurrent 2 Detection Voltage [V <sub>DIOV2</sub> ]	Overcurrent 1 Detection Delay Time [t <sub>DIOV1</sub> ]	Overcurrent 2 Detection Delay Time [t <sub>DIOV2</sub> ]	Overcurrent 3 Detection Function
S-8239BAA-M6T1U	0.20 V	0.4 V	1150 ms	0.56 ms	Unavailable

**Remark** Contact our sales representatives for products other than the above.

■ **Pin Configuration**

1. SOT-23-6



**Figure 2**

**Table 3**

Pin No.	Symbol	Description
1	VINI	Voltage detection pin between VINI pin and VSS pin (Overcurrent detection pin)
2	VM	Overcurrent latch pin
3	DO	Connection pin of discharge control FET gate
4	DP*1	Test pin for delay time measurement
5	VDD	Input pin for positive power supply
6	VSS	Input pin for negative power supply

\*1. The DP pin should be open.

\*1. The DP pin should be open.

■ **Absolute Maximum Ratings**

Table 4

(Ta = +25°C unless otherwise specified)

Item	Symbol	Applied pin	Absolute Maximum Rating	Unit
Input voltage between VDD pin and VSS pin	V <sub>DS</sub>	VDD	V <sub>SS</sub> - 0.3 to V <sub>SS</sub> +12	V
VM pin input voltage	V <sub>VM</sub>	VM	V <sub>DD</sub> - 28 to V <sub>DD</sub> + 0.3	V
VINI pin input voltage	V <sub>VINI</sub>	VINI	V <sub>SS</sub> - 0.3 to V <sub>SS</sub> + 12	V
DO pin output voltage	V <sub>DO</sub>	DO	V <sub>SS</sub> - 0.3 to V <sub>SS</sub> + 28	V
Power dissipation	P <sub>D</sub>	-	650*1	mW
Operation ambient temperature	T <sub>opr</sub>	-	-40 to +85	°C
Storage temperature	T <sub>stg</sub>	-	-55 to +125	°C

\*1. When mounted on board  
 [Mounted board]

- (1) Board size: 114.3 mm × 76.2 mm × t1.6 mm
- (2) Board name: JEDEC STANDARD51-7

**Caution**

1. The DP pin should be open.
2. The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

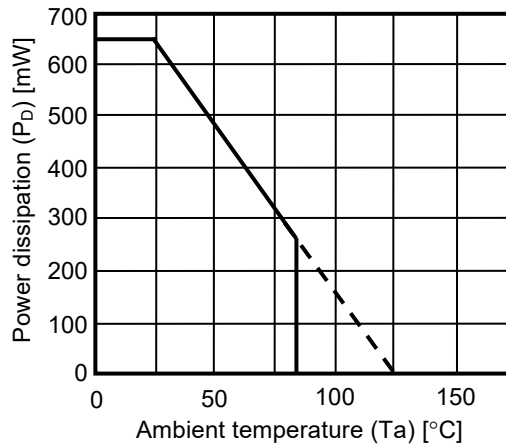


Figure 3 Power Dissipation of Package (When Mounted on Board)

■ **Electrical Characteristics**

1. Ta = +25°C

**Table 5**

(Ta = +25°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Condition	Test Circuit
<b>Detection Voltage</b>								
Overcurrent 1 detection voltage	V <sub>DIOV1</sub>	–	V <sub>DIOV1</sub> – 0.015	V <sub>DIOV1</sub>	V <sub>DIOV1</sub> + 0.015	V	1	1
Overcurrent 2 detection voltage*1	V <sub>DIOV2</sub>	–	V <sub>DIOV2</sub> – 0.100	V <sub>DIOV2</sub>	V <sub>DIOV2</sub> + 0.100	V	1	1
Overcurrent 3 detection voltage	V <sub>DIOV3</sub>	With overcurrent 3 detection function	0.90	1.20	1.50	V	1	1
UVLO detection voltage	V <sub>UVLO</sub>	–	1.90	2.00	2.10	V	1	1
<b>Release Voltage</b>								
Overcurrent release voltage	V <sub>RIOV</sub>	V <sub>DD</sub> criteria, V <sub>DD</sub> = 3.5 V	0.7	1.2	1.5	V	1	1
<b>Input Voltage, Operation Voltage</b>								
Operation voltage between VDD pin and VSS pin	V <sub>DSOP</sub>	Output logic is determined*2	1.5	–	8	V	–	–
<b>Current Consumption</b>								
Current consumption during normal operation	I <sub>OP</sub>	V <sub>DD</sub> = 3.5 V, V <sub>VM</sub> = 0 V	1.0	3.5	7.0	μA	2	2
Current consumption during power-down	I <sub>PDN</sub>	V <sub>DD</sub> = V <sub>VM</sub> = 1.5 V	–	–	0.1	μA	2	2
<b>Internal Resistance</b>								
Internal resistance between VM pin and VDD pin	R <sub>VMD</sub>	V <sub>DD</sub> = 1.8 V, V <sub>VM</sub> = 0 V	100	300	900	kΩ	3	3
<b>Output Resistance</b>								
DO pin resistance "L"	R <sub>DOL</sub>	V <sub>DD</sub> = V <sub>VINI</sub> = 3.5 V, V <sub>DO</sub> = 0.5 V	2.5	5	10	kΩ	4	4
<b>Delay Time</b>								
Overcurrent 1 detection delay time	t <sub>DIOV1</sub>	–	t <sub>DIOV1</sub> × 0.6	t <sub>DIOV1</sub>	t <sub>DIOV1</sub> × 1.4	ms	5	5
Overcurrent 2 detection delay time	t <sub>DIOV2</sub>	–	t <sub>DIOV2</sub> × 0.6	t <sub>DIOV2</sub>	t <sub>DIOV2</sub> × 1.4	ms	5	5
Overcurrent 3 detection delay time	t <sub>DIOV3</sub>	With overcurrent 3 detection function	168	280	392	μs	5	5
UVLO detection delay time	t <sub>UVLO</sub>	–	2.94	4.90	6.86	s	5	5

\*1. Even if overcurrent 1 detection voltage and overcurrent 2 detection voltage are in the same range, V<sub>DIOV1</sub> is lower than V<sub>DIOV2</sub>.

\*2. It indicates that DO pin output logic is determined.

**OVERCURRENT MONITORING IC FOR MULTI-SERIAL-CELL PACK**  
**S-8239B Series**

Rev.1.2\_00

2. Ta = -40°C to +85°C\*1

Table 6

(Ta = -40°C to +85°C\*1 unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Condition	Test Circuit
<b>Detection Voltage</b>								
Overcurrent 1 detection voltage	V <sub>DIOV1</sub>	-	V <sub>DIOV1</sub> - 0.021	V <sub>DIOV1</sub>	V <sub>DIOV1</sub> + 0.021	V	1	1
Overcurrent 2 detection voltage*2	V <sub>DIOV2</sub>	-	V <sub>DIOV2</sub> - 0.130	V <sub>DIOV2</sub>	V <sub>DIOV2</sub> + 0.130	V	1	1
Overcurrent 3 detection voltage	V <sub>DIOV3</sub>	With overcurrent 3 detection function	0.70	1.20	1.70	V	1	1
UVLO detection voltage	V <sub>UVLO</sub>	-	1.85	2.00	2.15	V	1	1
<b>Release Voltage</b>								
Overcurrent release voltage	V <sub>RIOV</sub>	V <sub>DD</sub> criteria, V <sub>DD</sub> = 3.5 V	0.5	1.2	1.7	V	1	1
<b>Input Voltage, Operation Voltage</b>								
Operation voltage between VDD pin and VSS pin	V <sub>DSOP</sub>	Output logic is determined*3	1.5	-	8	V	-	-
<b>Current Consumption</b>								
Current consumption during normal operation	I <sub>OPe</sub>	V <sub>DD</sub> = 3.5 V, V <sub>VM</sub> = 0 V	0.7	3.5	8.0	μA	2	2
Current consumption during power-down	I <sub>PDN</sub>	V <sub>DD</sub> = V <sub>VM</sub> = 1.5 V	-	-	0.15	μA	2	2
<b>Internal Resistance</b>								
Internal resistance between VM pin and VDD pin	R <sub>VMD</sub>	V <sub>DD</sub> = 1.8 V, V <sub>VM</sub> = 0 V	78	300	1310	kΩ	3	3
<b>Output Resistance</b>								
DO pin resistance "L"	R <sub>DOL</sub>	V <sub>DD</sub> = V <sub>VINI</sub> = 3.5 V, V <sub>DO</sub> = 0.5 V	1.2	5	15	kΩ	4	4
<b>Delay Time</b>								
Overcurrent 1 detection delay time	t <sub>DIOV1</sub>	-	t <sub>DIOV1</sub> × 0.2	t <sub>DIOV1</sub>	t <sub>DIOV1</sub> × 1.8	ms	5	5
Overcurrent 2 detection delay time	t <sub>DIOV2</sub>	-	t <sub>DIOV2</sub> × 0.2	t <sub>DIOV2</sub>	t <sub>DIOV2</sub> × 1.8	ms	5	5
Overcurrent 3 detection delay time	t <sub>DIOV3</sub>	With overcurrent 3 detection function	56	280	504	μs	5	5
UVLO detection delay time	t <sub>UVLO</sub>	-	0.98	4.90	8.82	s	5	5

\*1. Since products are not screened at high and low temperatures, the specification for this temperature range is guaranteed by design, not tested in production.

\*2. Even if overcurrent 1 detection voltage and overcurrent 2 detection voltage are in the same range, V<sub>DIOV1</sub> is lower than V<sub>DIOV2</sub>.

\*3. It indicates that DO pin output logic is determined.

## ■ Test Circuits

**Caution** Unless otherwise specified, the output voltage levels "H" and "L" at the DO pin ( $V_{DO}$ ) are judged by the threshold voltage (1.0 V) of the N-channel FET. Judge the DO pin level with respect to  $V_{SS}$ .

### 1. Overcurrent 1 detection voltage, overcurrent 2 detection voltage, overcurrent release voltage, UVLO detection voltage (Test condition 1, test circuit 1)

The overcurrent 1 detection voltage ( $V_{DIOV1}$ ) is defined as the voltage  $V_2$  whose delay time for changing  $V_{DO}$  from "H" to "L" lies between the minimum and the maximum value of the overcurrent 1 detection delay time after the voltage  $V_2$  is increased instantaneously (within 10  $\mu$ s) from the set conditions of  $V_1 = V_3 = 3.5$  V,  $V_2 = 0$  V.

The overcurrent 2 detection voltage ( $V_{DIOV2}$ ) is defined as the voltage  $V_2$  whose delay time for changing  $V_{DO}$  from "H" to "L" lies between the minimum and the maximum value of the overcurrent 2 detection delay time after the voltage  $V_2$  is increased instantaneously (within 10  $\mu$ s) from the set conditions of  $V_1 = V_3 = 3.5$  V,  $V_2 = 0$  V.

The overcurrent release voltage ( $V_{RIOV}$ ) is defined as the voltage  $V_3$  at which  $V_{DO}$  goes from "L" to "H" after decreasing  $V_2$  to 0 V and the voltage  $V_3$  is increased gradually from the set conditions of  $V_1 = V_2 = 3.5$  V,  $V_3 = 0$  V.

The UVLO detection voltage ( $V_{UVLO}$ ) is defined as the voltage  $V_1$  at which  $V_{DO}$  goes from "H" to "L" after the voltages  $V_1$  and  $V_3$  are decreased gradually from the set conditions of  $V_1 = V_3 = 3.5$  V,  $V_2 = 0$  V.

### 2. Overcurrent 3 detection voltage (With overcurrent 3 detection function) (Test condition 1, test circuit 1)

The overcurrent 3 detection voltage ( $V_{DIOV3}$ ) is defined as the voltage  $V_2$  whose delay time for changing  $V_{DO}$  from "H" to "L" lies between the minimum and the maximum value of the overcurrent 3 detection delay time after the voltage  $V_2$  is increased instantaneously (within 10  $\mu$ s) from the set conditions of  $V_1 = V_3 = 3.5$  V,  $V_2 = 0$  V.

### 3. Current consumption during normal operation, current consumption during power-down (Test condition 2, test circuit 2)

The current consumption during normal operation ( $I_{OPE}$ ) is the current that flows through the VDD pin ( $I_{DD}$ ) under the set conditions of  $V_1 = 3.5$  V,  $V_2 = 0$  V.

The current consumption during power-down ( $I_{PDN}$ ) is  $I_{DD}$  under the set conditions of  $V_1 = V_2 = 1.5$  V.

### 4. Internal resistance between VM pin and VDD pin (Test condition 3, test circuit 3)

The internal resistance between the VM pin and the VDD pin ( $R_{VMD}$ ) is the resistance between the VM pin and the VDD pin under the set conditions of  $V_1 = 1.8$  V,  $V_2 = V_3 = 0$  V.

### 5. DO pin resistance "L" (Test condition 4, test circuit 4)

The DO pin resistance "L" ( $R_{DOL}$ ) is the DO pin resistance under the set conditions of  $V_1 = V_2 = 3.5$  V,  $V_3 = 0.5$  V.



**6. Overcurrent 1 detection delay time**  
**(Test condition 5, test circuit 5)**

**6.1  $V_{DIOV2} = 0.1\text{ V}$**

The overcurrent 1 detection delay time ( $t_{DIOV1}$ ) is the time period from when the voltage V2 exceeds  $V_{DIOV1}$  to when  $V_{DO}$  goes to "L", after V2 is increased to 0.08 V instantaneously (within 10  $\mu\text{s}$ ) under the set conditions of  $V1 = 3.5\text{ V}$ ,  $V2 = 0\text{ V}$ .

**6.2  $V_{DIOV2} \geq 0.2\text{ V}$**

The overcurrent 1 detection delay time ( $t_{DIOV1}$ ) is the time period from when the voltage V2 exceeds  $V_{DIOV1}$  to when  $V_{DO}$  goes to "L", after V2 is increased to  $V_{DIOV1}\text{ max.} + 0.01\text{ V}$  instantaneously (within 10  $\mu\text{s}$ ) under the set conditions of  $V1 = 3.5\text{ V}$ ,  $V2 = 0\text{ V}$ .

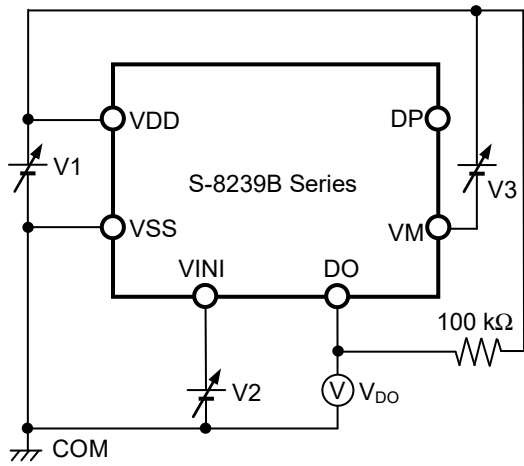
**7. Overcurrent 2 detection delay time, UVLO detection delay time**  
**(Test condition 5, test circuit 5)**

The overcurrent 2 detection delay time ( $t_{DIOV2}$ ) is the time period from when the voltage V2 exceeds  $V_{DIOV2}$  to when  $V_{DO}$  goes to "L", after V2 is increased to 0.9 V instantaneously (within 10  $\mu\text{s}$ ) under the set conditions of  $V1 = 3.5\text{ V}$ ,  $V2 = 0\text{ V}$ .

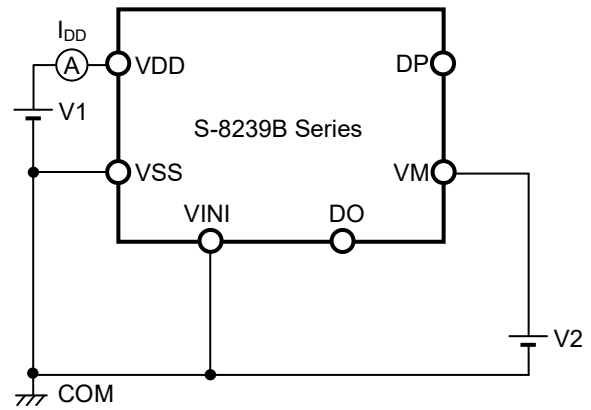
The UVLO detection delay time ( $t_{UVLO}$ ) is the time period from when the voltage V1 falls below  $V_{UVLO}$  to when  $V_{DO}$  goes to "L", after V1 is decreased to 1.8 V instantaneously (within 10  $\mu\text{s}$ ) under the set conditions of  $V1 = 3.5\text{ V}$ ,  $V2 = 0\text{ V}$ .

**8. Overcurrent 3 detection delay time (With overcurrent 3 detection function)**  
**(Test condition 5, test circuit 5)**

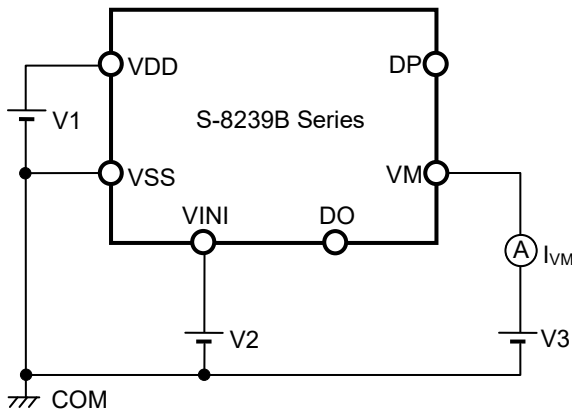
The overcurrent 3 detection delay time ( $t_{DIOV3}$ ) is the time period from when the voltage V2 exceeds  $V_{DIOV3}$  to when  $V_{DO}$  goes to "L", after V2 is increased to 1.6 V instantaneously (within 10  $\mu\text{s}$ ) under the set conditions of  $V1 = 3.5\text{ V}$ ,  $V2 = 0\text{ V}$ .



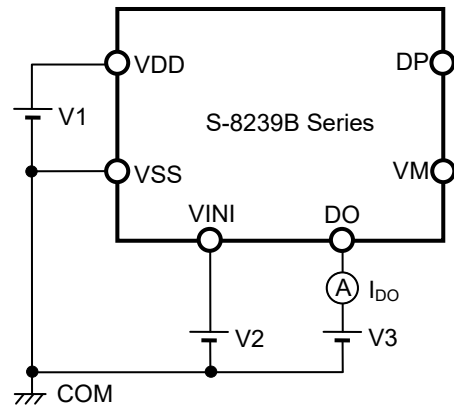
**Figure 4 Test Circuit 1**



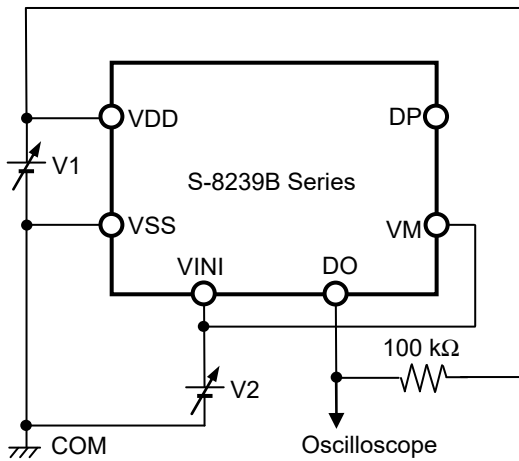
**Figure 5 Test Circuit 2**



**Figure 6 Test Circuit 3**



**Figure 7 Test Circuit 4**



**Figure 8 Test Circuit 5**

## ■ Operation

### 1. Normal status

The S-8239B Series monitors the voltage between the VINI pin and the VSS pin to control discharging. When the VINI pin voltage is equal to or lower than the overcurrent 1 detection voltage ( $V_{DIOV1}$ ), the DO pin becomes "High-Z". This status is called the normal status.

**Caution** When a battery is connected for the first time, the S-8239B Series may not be in the normal status. In this case, short the VM pin and VSS pin or connect the charger. The S-8239B Series then becomes the normal status.

### 2. Overcurrent status (Overcurrent 1, overcurrent 2, overcurrent 3)

When a battery is in the normal status, if the VINI pin voltage is equal to or higher than the overcurrent detection voltage because the discharge current is equal to or higher than the specified value and the status continues for the overcurrent detection delay time or longer, the DO pin becomes  $V_{SS}$  potential. This status is called the overcurrent status. The overcurrent status is retained when the voltage between the VDD pin and the VM pin is equal to or lower than the overcurrent release voltage ( $V_{RIOV}$ ).

In the overcurrent status, the VM pin and the VDD pin are shorted by the internal resistance between the VM pin and the VDD pin ( $R_{VMD}$ ) in the S-8239B Series.

After that, the overcurrent status is released if the voltage between the VDD pin and the VM pin becomes equal to or higher than  $V_{RIOV}$  by connecting a charger.

### 3. UVLO status

The S-8239B Series includes a UVLO (under voltage lock out) function to prevent the IC malfunction due to the decrease of the battery voltage when detecting the overcurrent. When the battery voltage in the normal status is equal to or lower than the UVLO detection voltage ( $V_{UVLO}$ ) and the status continues for the UVLO detection delay time ( $t_{UVLO}$ ) or longer, the DO pin becomes  $V_{SS}$  potential. This status is called the UVLO status.

In the UVLO status, the VM pin and the VDD pin are shorted by  $R_{VMD}$  between the VM pin and the VDD pin in the S-8239B Series.

After that, the UVLO status is released if the battery voltage becomes equal to or higher than  $V_{UVLO}$ .

### 4. Power-down status

In the UVLO status, the current consumption is decreased to the current consumption during power-down ( $I_{PDN}$ ) if the voltage between the VDD pin and the VM pin becomes equal to or lower than 0.7 V typ. in the S-8239B Series. This status is called the power-down status.

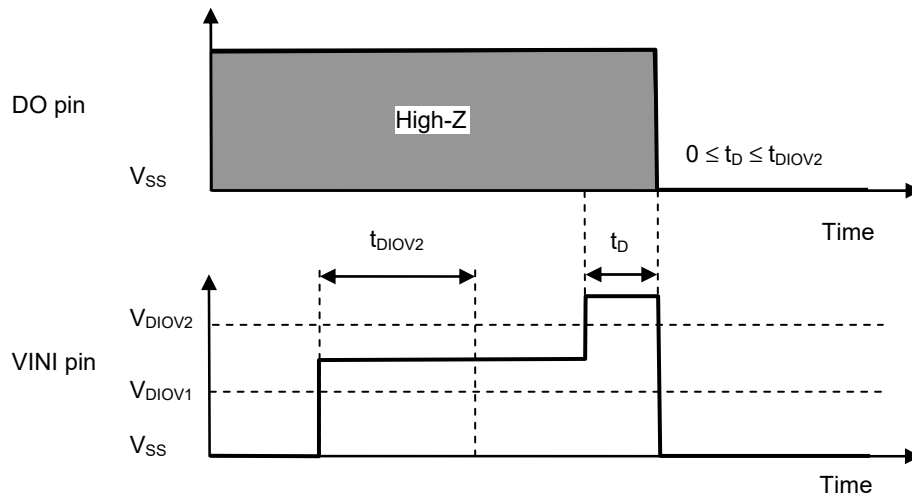
Moreover, if the voltage between the VDD pin and the VM pin becomes equal to or lower than 0.7 V typ. and the status continues for  $t_{UVLO}$  or longer in the normal status, the DO pin becomes  $V_{SS}$  potential and the S-8239B Series becomes power-down status.

After that, the power-down status is released if the voltage between the VDD pin and the VM pin is equal to or higher than 0.7 V typ. by connecting a charger.

**5. Delay circuit**

The detection delay times are determined by dividing a clock of approximately 3.5 kHz with the counter.

**Remark** The overcurrent 2 detection delay time ( $t_{DIOV2}$ ) starts when the overcurrent 1 detection voltage ( $V_{DIOV1}$ ) is detected. When the overcurrent 2 detection voltage ( $V_{DIOV2}$ ) is detected over  $t_{DIOV2}$  after the detection of  $V_{DIOV1}$ , the S-8239B Series becomes the overcurrent status within  $t_D$  from the time of detecting  $V_{DIOV2}$ .



**Figure 9**

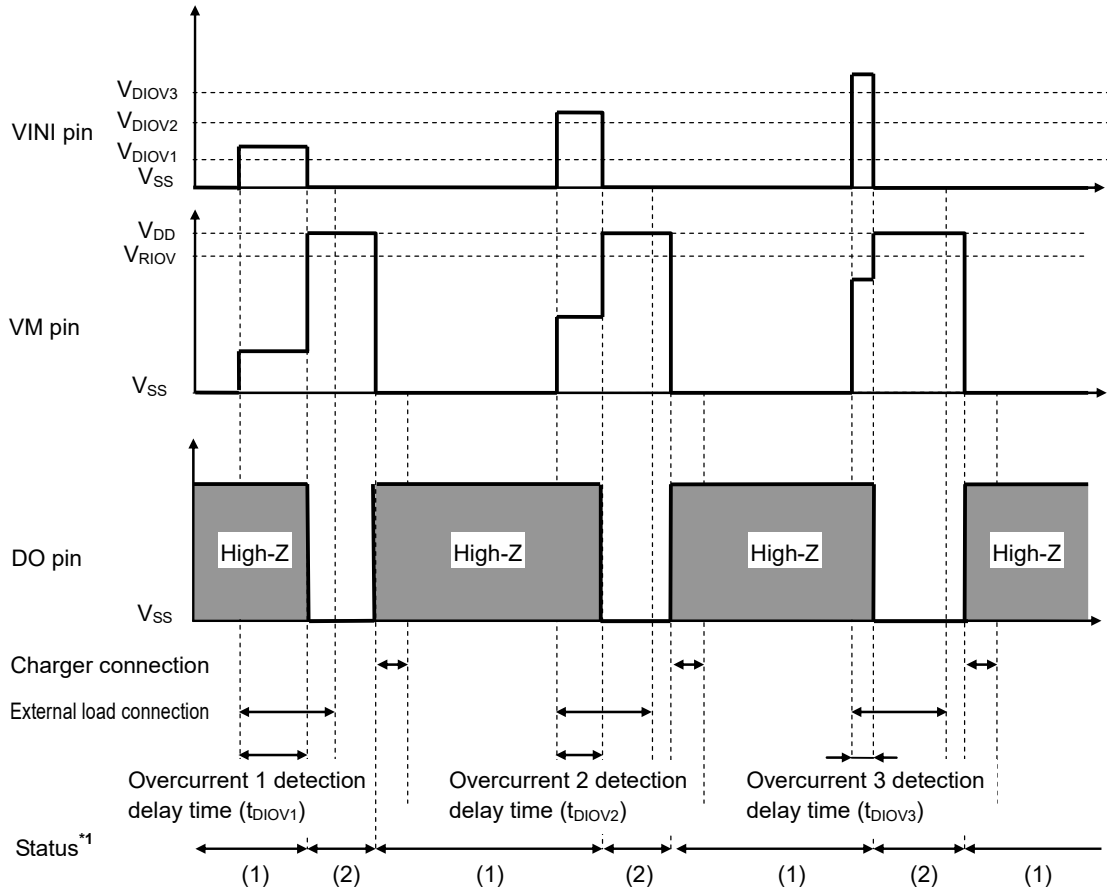
**6. DP pin**

The DP pin is a test pin for delay time measurement and it should be open in the actual application. If a capacitor whose capacitance is 1000 pF or more or a resistor whose resistance is 1 MΩ or less is connected to this pin, error may occur in the delay times or in the detection voltages.

■ Timing Charts

1. Overcurrent detection

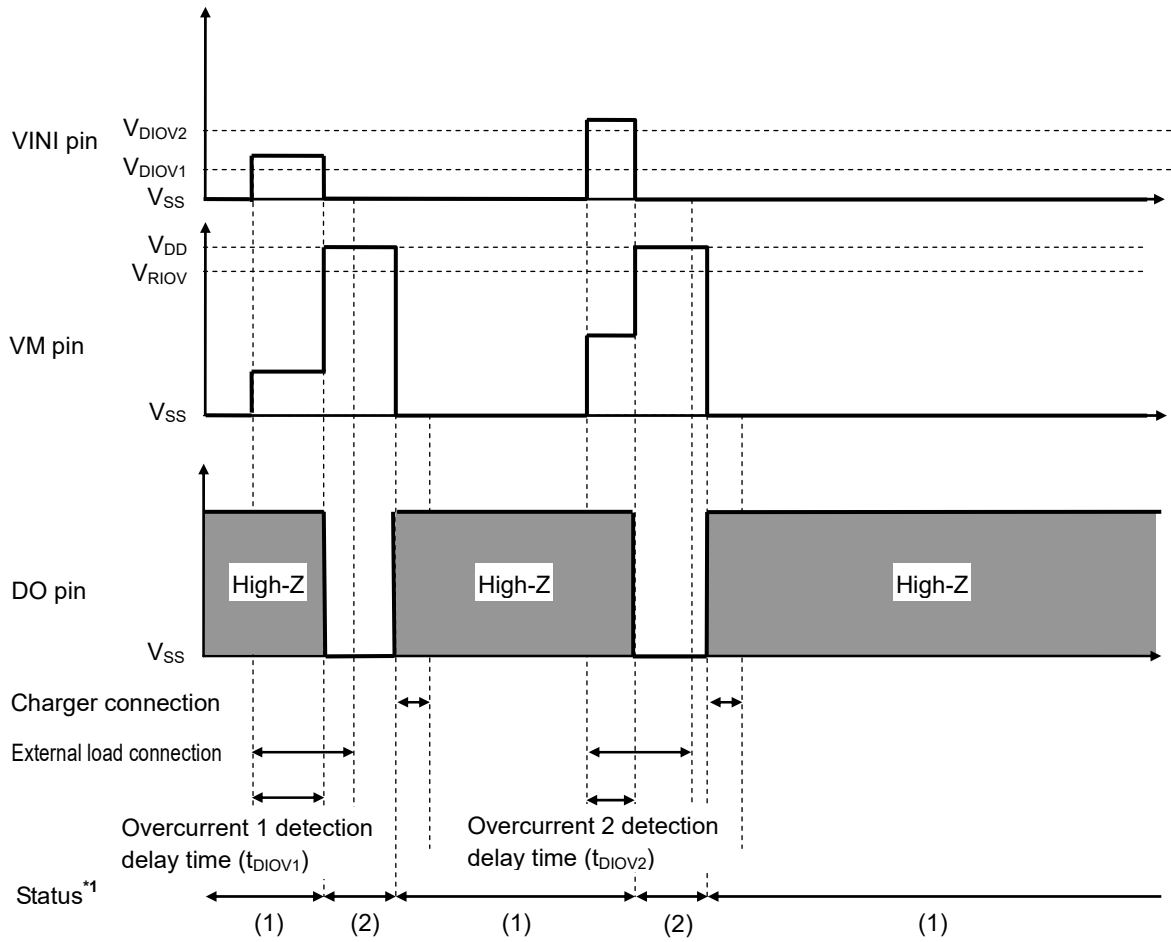
1.1 With overcurrent 3 detection function



\*1. (1): Normal status  
(2): Overcurrent status

Figure 10

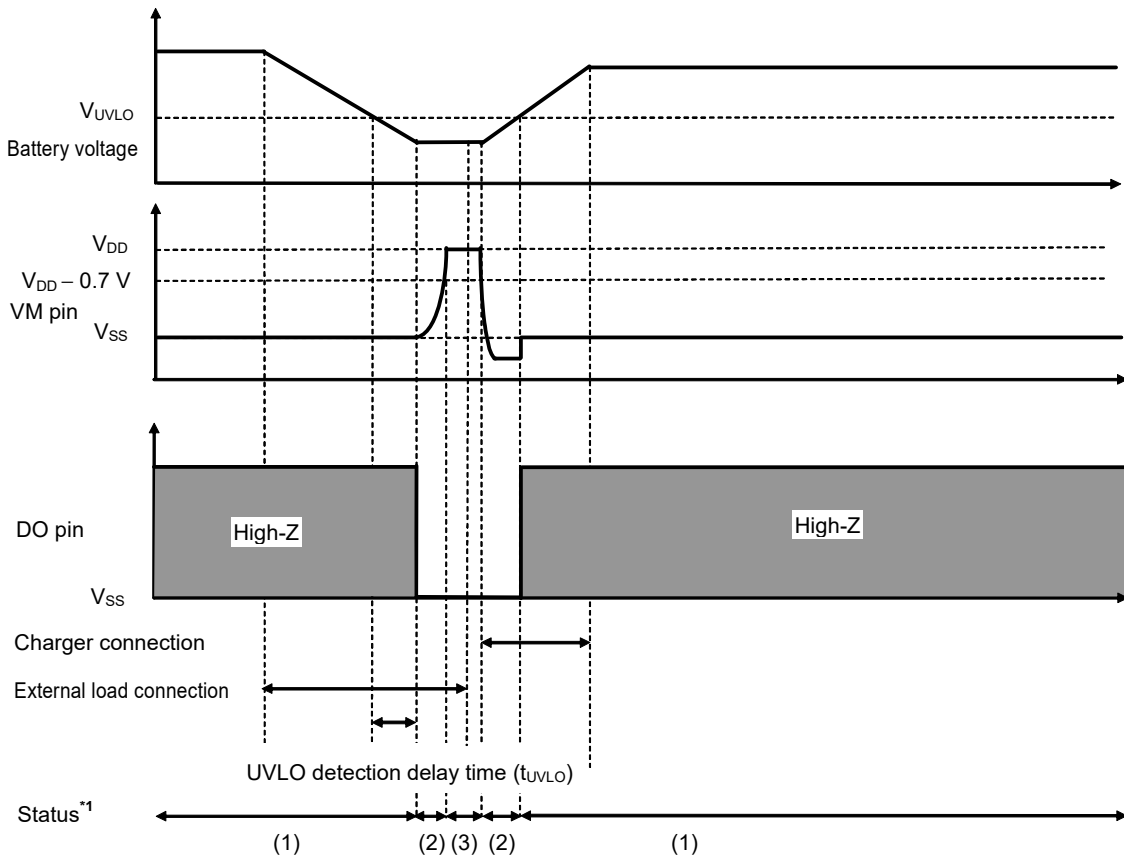
1. 2 Without overcurrent 3 detection function



\*1. (1): Normal status  
 (2): Overcurrent status

Figure 11

**2. UVLO detecion**



- \*1. (1): Normal status  
 (2): UVLO status  
 (3): Power-down status

**Remark** The charger is assumed to charge with a constant current.

**Figure 12**

■ **5-serial-cell Protection Circuit Example**

Figure 13 shows the 5-serial-cell protection circuit example used by the S-8239B Series and the S-8225A Series. Contact our sales representatives when using the circuit other than the following protection circuit example.

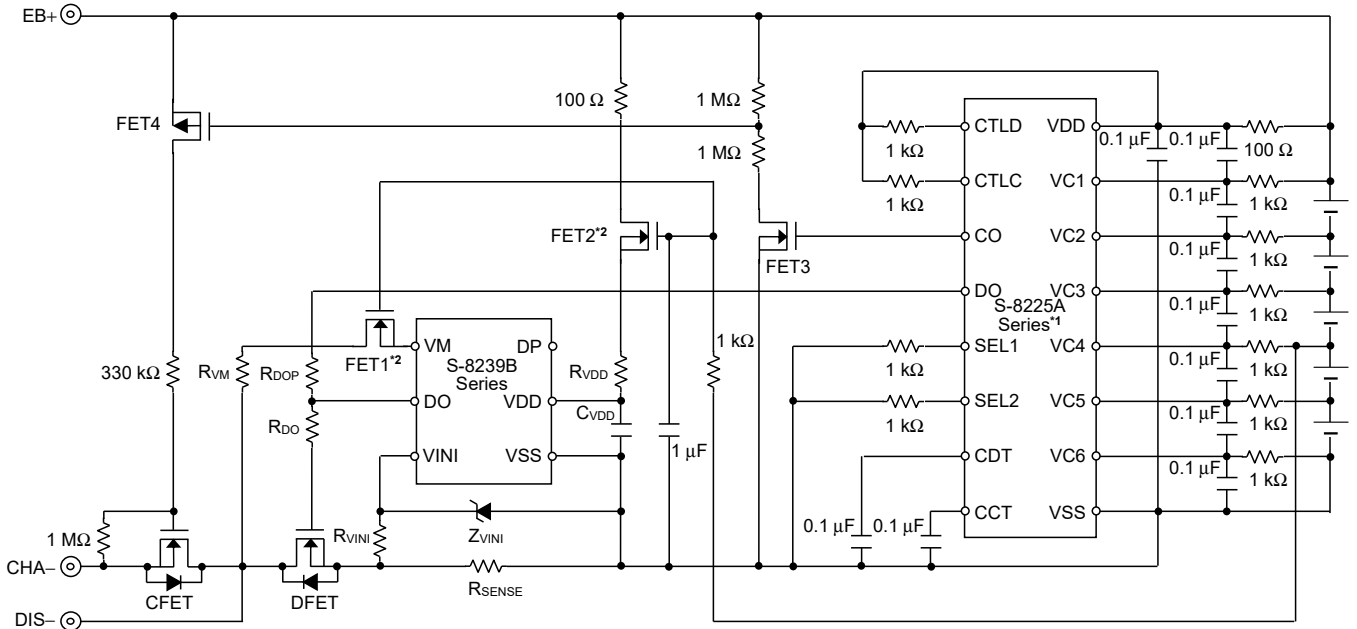


Figure 13

Table 7 Constants for External Components

Symbol	Min.	Typ.	Max.	Unit
$R_{VDD}$	300	470	1000	$\Omega$
$R_{VINI}$	1	–	–	k $\Omega$
$R_{SENSE}$	0	–	–	m $\Omega$
$R_{VM}$	1	5.1	51	k $\Omega$
$R_{DO}^{*3}$	–	5.1	–	k $\Omega$
$R_{DOP}$	330	510	2000	k $\Omega$
$C_{VDD}$	0.022	0.1	1	$\mu F$

\*1. Refer to the data sheet of the S-8225A Series for the recommended value for external components of the S-8225A Series.

\*2. Use the products with the same model number for FET1 and FET2.

\*3. Set up the optimal constant according to the FET in use.

**Caution 1. The constants may be changed without notice.**

2. It has not been confirmed whether the operation is normal or not in circuits other than the connection example. In addition, the connection example and the constants do not guarantee proper operation. Perform thorough evaluation using the actual application to set the constants.
3. The DP pin should be open.



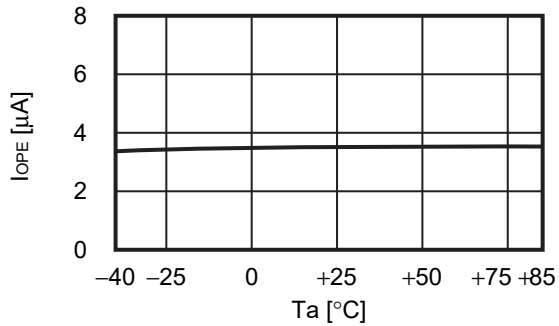
## ■ Precautions

- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any and all disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

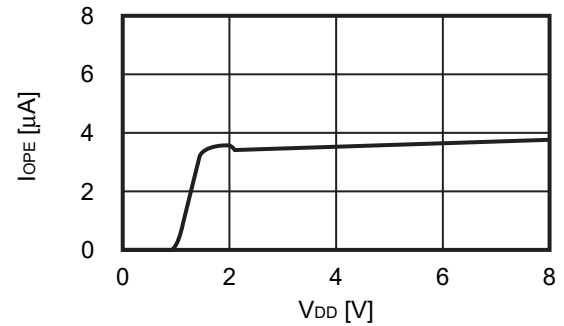
■ Characteristics (Typical Data)

1. Current consumption

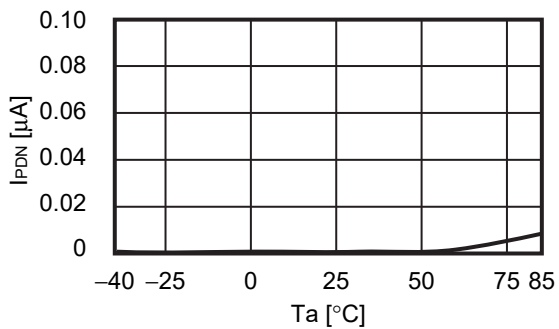
1. 1 I<sub>OPe</sub> vs. T<sub>a</sub>



1. 2 I<sub>OPe</sub> vs. V<sub>DD</sub>

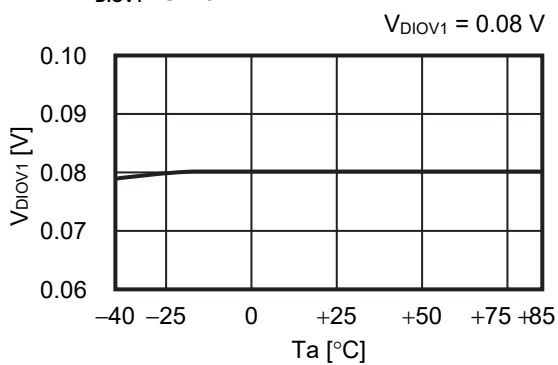


1. 3 I<sub>PDN</sub> vs. T<sub>a</sub>

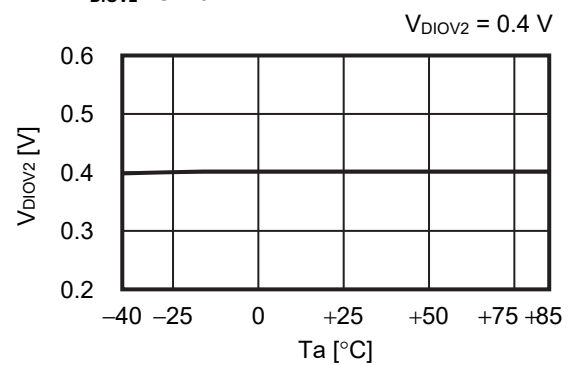


2. Overcurrent detection / release voltage, UVLO function and delay times

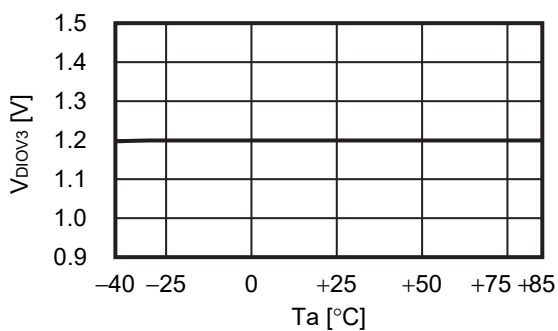
2. 1 V<sub>DIOV1</sub> vs. T<sub>a</sub>



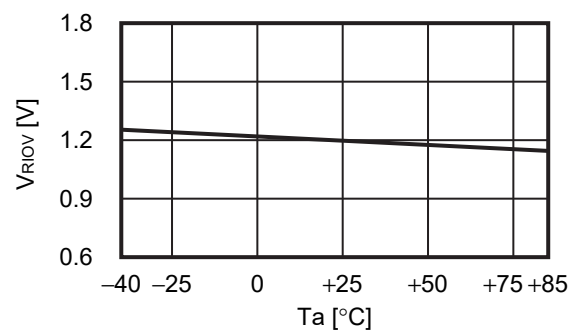
2. 2 V<sub>DIOV2</sub> vs. T<sub>a</sub>



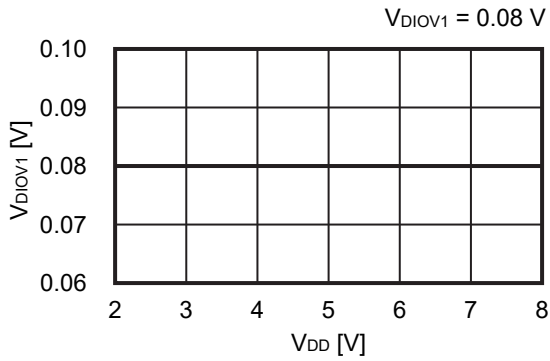
2. 3 V<sub>DIOV3</sub> vs. T<sub>a</sub>



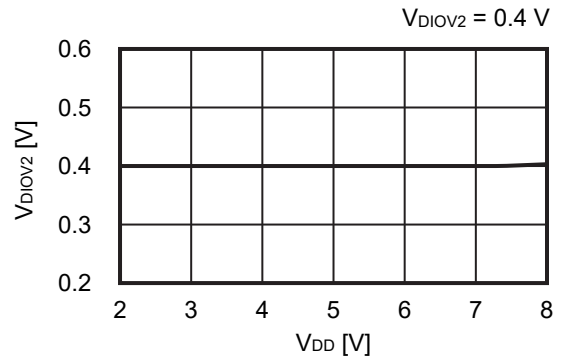
2. 4 V<sub>RIOV</sub> vs. T<sub>a</sub>



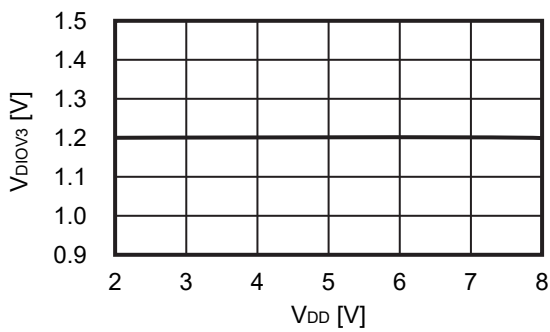
**2.5  $V_{DIOV1}$  vs.  $V_{DD}$**



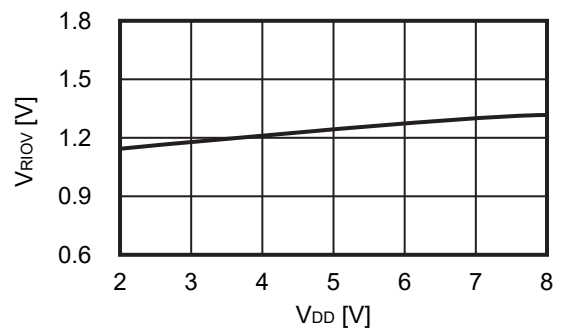
**2.6  $V_{DIOV2}$  vs.  $V_{DD}$**



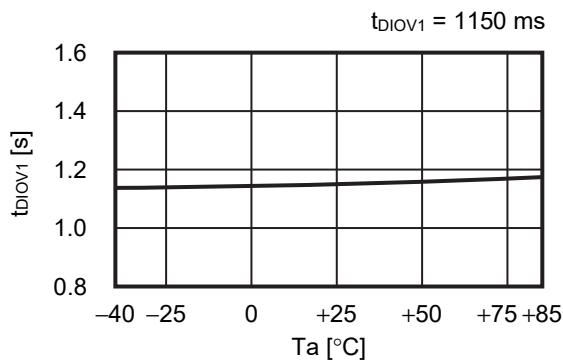
**2.7  $V_{DIOV3}$  vs.  $V_{DD}$**



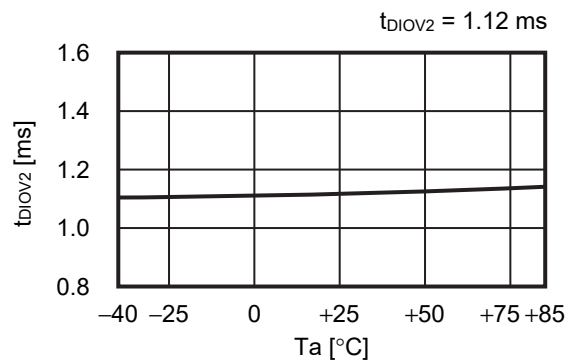
**2.8  $V_{RIOV}$  vs.  $V_{DD}$**



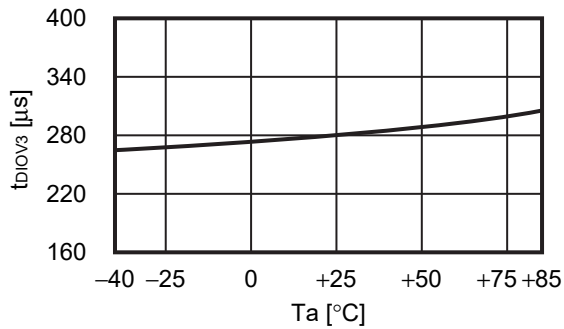
**2.9  $t_{DIOV1}$  vs.  $T_a$**



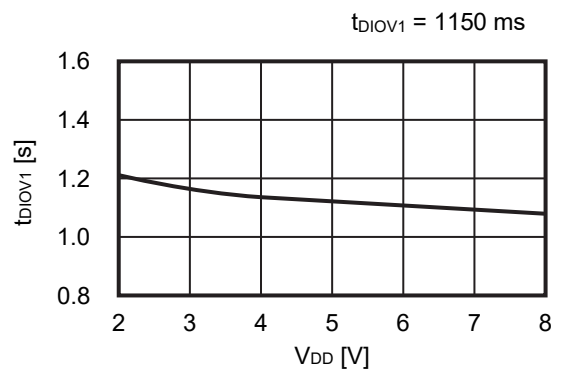
**2.10  $t_{DIOV2}$  vs.  $T_a$**



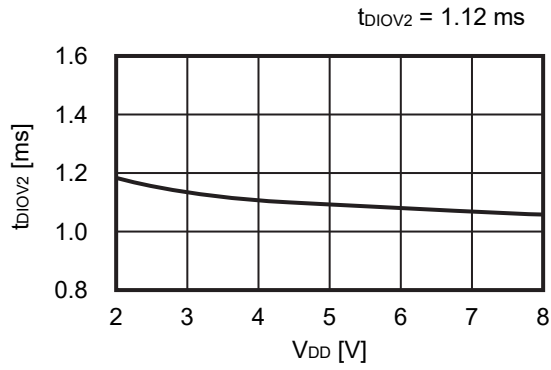
**2.11  $t_{DIOV3}$  vs.  $T_a$**



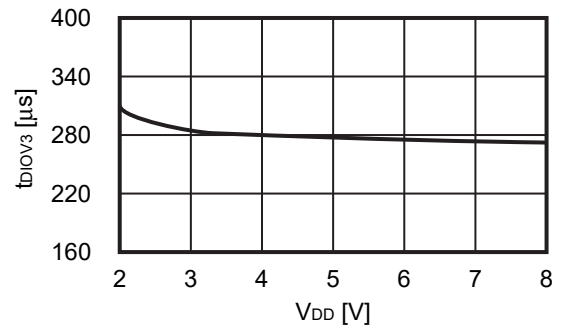
**2.12  $t_{DIOV1}$  vs.  $V_{DD}$**



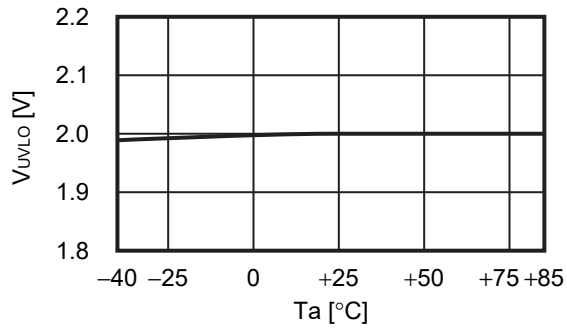
**2. 13  $t_{DIOV2}$  vs.  $V_{DD}$**



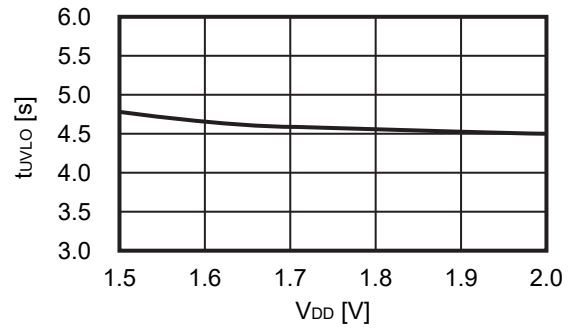
**2. 14  $t_{DIOV3}$  vs.  $V_{DD}$**



**2. 15  $V_{UVLO}$  vs.  $T_a$**

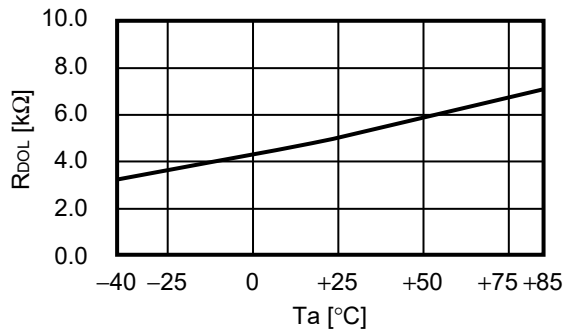


**2. 16  $t_{UVLO}$  vs.  $V_{DD}$**



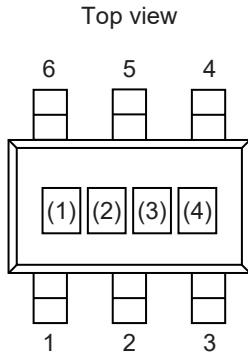
**3. Output Resistance**

**3. 1  $R_{DOL}$  vs.  $T_a$**



■ **Marking Specification**

1. **SOT-23-6**



(1) to (3): Product code (Refer to **Product name vs. Product code**)  
 (4): Lot number

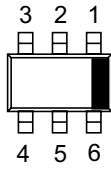
**Product name vs. Product code**

Product Name	Product Code		
	(1)	(2)	(3)
S-8239BAA-M6T1U	3	L	A



No. MP006-A-P-SD-2.1

TITLE	SOT236-A-PKG Dimensions
No.	MP006-A-P-SD-2.1
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	



No. MP006-A-C-SD-3.1

TITLE	SOT236-A-Carrier Tape
No.	MP006-A-C-SD-3.1
ANGLE	
UNIT	mm
<b>ABLIC Inc.</b>	



Enlarged drawing in the central part



No. MP006-A-R-SD-2.1

TITLE	SOT236-A-Reel		
No.	MP006-A-R-SD-2.1		
ANGLE		QTY	3,000
UNIT	mm		
<b>ABLIC Inc.</b>			



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2.4-2019.07